

< C band internally matched power GaAs FET >

MGFC39V4450A

4.4 - 5.0 GHz BAND / 8W

DESCRIPTION

The MGFC39V4450A is an internally impedance-matched GaAs power FET especially designed for use in 4.4-5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

P1dB=8W (TYP.) @f=4.4 – 5.0GHz

High power gain

GLP=11.5dB (TYP.) @f=4.4 - 5.0GHz

P.A.E.=30% (TYP.) @f=4.4 - 5.0GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=28dBm S.C.L

APPLICATION

 \bullet item 01 : 4.4 – 5.0 GHz band power amplifier

• item 51: 4.4 – 5.0 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure • RG=50ohm

Absolute maximum ratings (Ta=25°C)

Parameter	Ratings	Unit
Gate to drain breakdown voltage	-15	V
Gate to source breakdown voltage	-15	V
Drain current	7.5	Α
Reverse gate current	-20	mA
Forward gate current	42	mA
Total power dissipation	42.8	W
Cannel temperature	175	°C
Storage temperature	-65 to +175	°C
	Gate to drain breakdown voltage Gate to source breakdown voltage Drain current Reverse gate current Forward gate current Total power dissipation Cannel temperature	Gate to drain breakdown voltage Gate to source breakdown voltage -15 Drain current 7.5 Reverse gate current -20 Forward gate current 42 Total power dissipation 42.8 Cannel temperature 175 Storage temperature -65 to +175

*1: Tc=25°C

OUTLINE DRAWING Unit: millimeters 21.0 +/-0.3 (1) (2) (2) (3) 10.7 17.0 +/-0.2 (1) GATE (2) SOURCE (FLANGE) (3) DRAIN

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Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	7.5	Α
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38	39	-	dBm
GLP	Linear Power Gain	f=4.4 - 5.0GHz	8	11.5	-	dB
ID	Drain current		-	-	3	Α
P.A.E.	Power added efficiency		-	30	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	=	3.5	°C/W

^{*2 :}item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=5.0GHz,delta f=10MHz

^{*3:} Channel-case

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